

CMPE 314 Midterm Exam 2

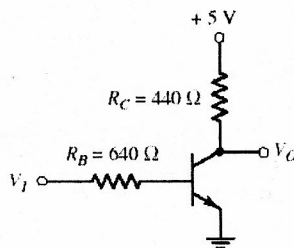
(April 19, 2011)

Problem 1. (15 points) - drawing & description

- What are the conditions for the cutoff, forward-active, and saturation modes for a pnp bipolar transistor? Show the structure, biasing connections.
- What are the charge carrier contributions to the emitter, collector and base currents (show directions)?

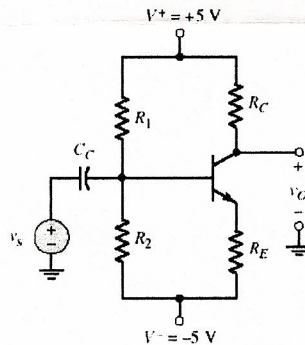
Problem 2. (20 points) - numerical answer

The transistor in the circuit has $\beta=50$, $V_{BE(on)}=0.7$ V and $V_{CE(sat)}=0.2$ V. Determine I_B , I_C , and the power dissipated in the transistor for $V_I=3.6$ V. Is the transistor in the forward-active mode?



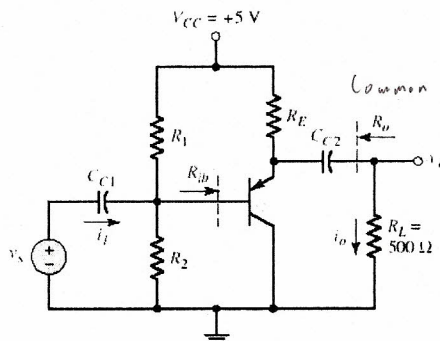
Problem 3. (25 points) - equations

Derive the equations for I_{CQ} and V_{CEQ} . Comment on the role of R_E . What is the maximum collector current under symmetric swing.



Problem 4. (40 points) - equations

- Assume finite V_A . Draw the AC equivalent circuit, including the hybrid- π model.
- Find the DC load-line slope and the AC load-line slope.
- Find the small-signal voltage gain and input resistance. Comment on the type of amplifier configuration and output resistance.

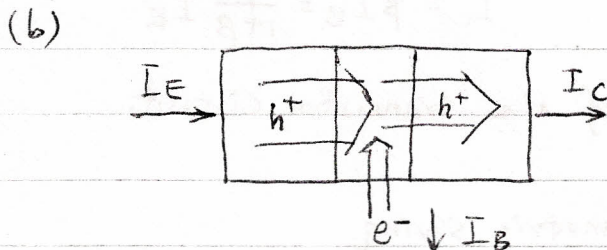
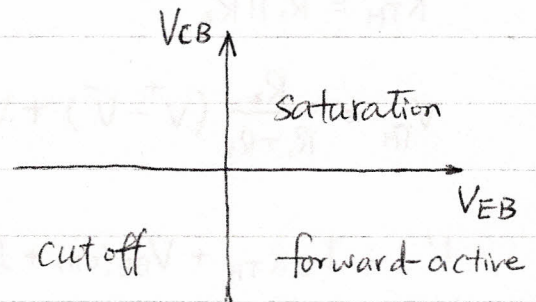
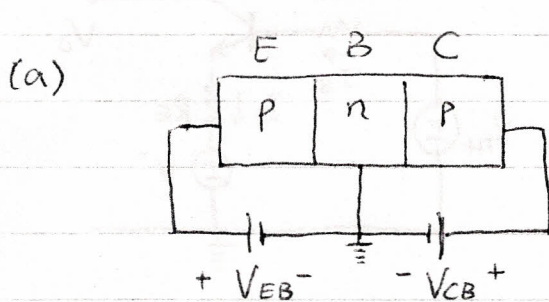


Common Em: HET $A_v \gg 1$
 $A_i \gg 1$
 Input \rightarrow Moderate
 Output \rightarrow Moderate \rightarrow High

Solutions to Midterm Exam II

CMPE 314
Spring 2011

Problem 1



I_E, I_C : Holes contribute most.
 I_B : Electrons contribute most.

Problem 2

$$V_I = I_B R_B + V_{BE(on)} \quad (V_I = 3.6V) \rightarrow I_B = \frac{3.6 - 0.7}{640} = 4.53 \text{ mA}$$

If $I_C = \beta I_B = 50 \times 4.53 \text{ mA} = 226.56 \text{ mA}$

then

$$V_{CE} = V^+ - I_C R_C = 5 - 99.66 = -94.66 \text{ V} \quad \text{not possible.}$$

Transistor is in saturation

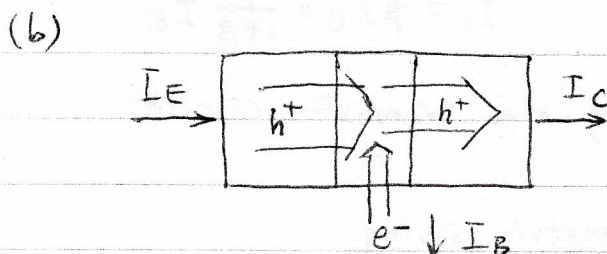
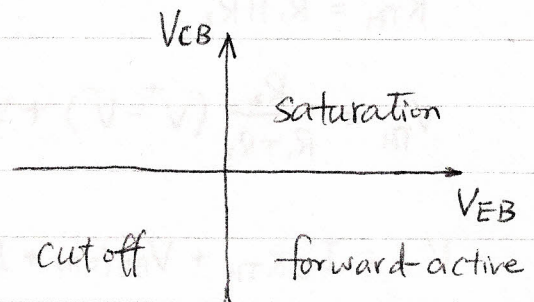
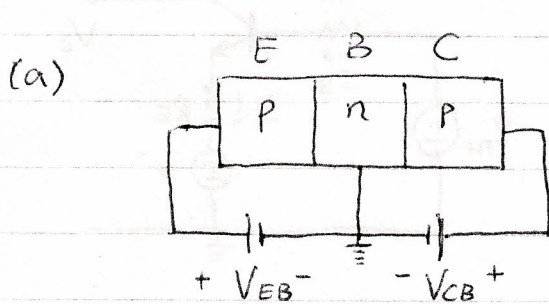
$$I_C = \frac{V^+ - V_{CE(sat)}}{R_C} = \frac{5 - 0.2}{440} = 10.91 \text{ mA}$$

$$P_{DC} = I_E V_{CE(sat)} + I_C V_{CE(sat)} = 3.01 + 3.18 = 6.19 \text{ mW}$$

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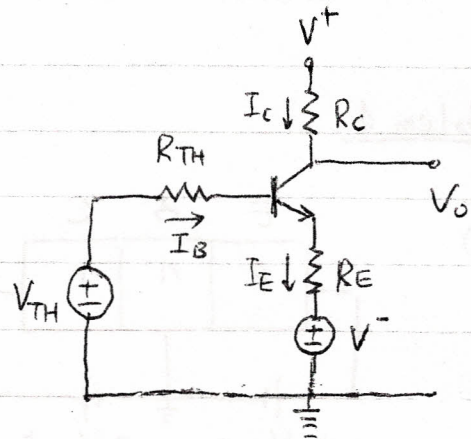
$$P_Q = I_B V_{BE(on)} + I_C V_{CE(sat)} = 3.71 + 2.182 = 5.353 \text{ mW}$$

Problem 3

$$R_{TH} = R_1 \parallel R_2$$

$$V_{TH} = \frac{R_2}{R_1 + R_2} (V^+ - V^-) + V^-$$

$$V_{TH} = I_B R_{TH} + V_{BE(on)} + I_E R_E + V^-$$



$$V^+ - V^- = I_C R_C + I_E R_E + V_{CE}$$

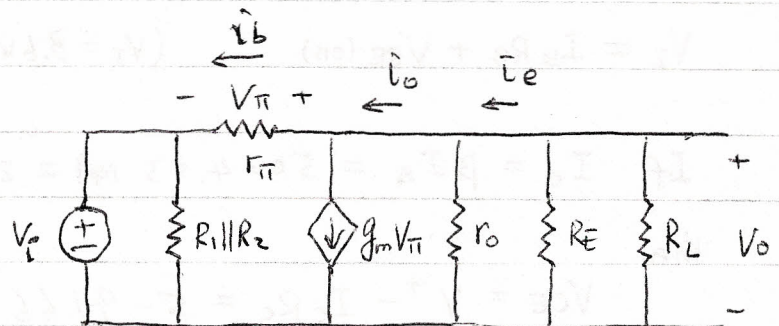
$$I_C = \beta I_B = \frac{\beta}{1 + \beta} I_E$$

R_E is to stabilize the Q-pt of the transistor circuit.

$$\hat{I}_{C,max} = 2 I_{CQ} \quad \text{under symmetric swing}$$

Problem 4

(a)



(b)

$$\text{DC: } V^+ = I_E R_E + V_{EC} = \frac{I_C}{\alpha} R_E + V_{EC}$$

$$\text{slope, DC} = - \frac{\alpha}{R_E}$$

$$\text{AC: slope, AC} = - \frac{\alpha}{r_o \parallel R_E \parallel R_L}$$

$$(c) \quad U_o = -\bar{i}_o (r_o \parallel R_E \parallel R_L) = -(1+\beta)(r_o \parallel R_E \parallel R_L) \bar{i}_b \quad \beta \bar{i}_b = g_m U_\pi$$

$$V_o = -V_\pi + U_o = -r_\pi \bar{i}_b - (1+\beta)(r_o \parallel R_E \parallel R_L) \bar{i}_b$$

$$A_v = \frac{U_o}{V_i} = \frac{(1+\beta)(r_o \parallel R_E \parallel R_L)}{r_\pi + (1+\beta)(r_o \parallel R_E \parallel R_L)}$$

$$R_{ib} = -\frac{V_i}{\bar{i}_b} = r_\pi + (1+\beta)(r_o \parallel R_E \parallel R_L)$$

It is an emitter-follower circuit.

$A_v \approx +1$. R_o is small.